

AMENDMENTS TO THE CLAIMS

The following listing of Claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-16. (Canceled).

17. (Previously Presented) A trench structure formed in a semiconductor substrate comprising:
an upper portion of said trench having an upper polygonal cross section; a lower portion of said trench having a lower polygonal cross section comprising four straight main sides oriented with an angular difference between consecutive main sides; four inner projecting corners disposed between said four main sides, said four inner corners being located closer to a center of said polygonal cross section than said main sides; connecting lines connecting said inner corners with said main sides; and said lower polygonal cross section having a greater number of sides than said upper polygonal cross section.

18. (Previously Presented) A capacitor formed in a trench in a semiconductor substrate comprising:
an upper portion of said trench having an upper polygonal cross section; a lower portion of said trench having a lower polygonal cross section comprising four straight main sides oriented with an angular difference between consecutive main sides; four inner projecting corners disposed between said four main sides, said four inner corners being located closer to a center of said polygonal cross section than said main sides; and connecting lines connecting said inner corners with said main sides; said lower polygonal cross section having a greater number of sides than said upper polygonal cross section; a node dielectric disposed on interior surfaces of said lower portion of said trench; and a conductive center electrode disposed within said trench and abutting said node dielectric.

19. (Canceled).

20. (Original) A capacitor according to claim 18, further comprising a transistor formed within said upper portion of said trench connected between said center electrode and a first cell contact, said transistor being controlled by a gate connected to a second cell contact, said capacitor and said transistor together thereby forming a DRAM cell.

21. (Canceled).

22. (Canceled).